BLC9G10XS-120A

Power LDMOS transistor Rev. 1 — 29 November 2018

AMPLEON

Product data sheet

Product profile 1.

1.1 General description

120 W LDMOS power transistor for base station applications at frequencies from 920 MHz to 960 MHz.

Typical performance

Typical RF performance at T_{case} = 25 °C in an asymmetrical Doherty application demo circuit.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	G _p	η _D	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	925 to 960	150	28	18	20	50	-28 ^[1]

^[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 10.5 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for broadband operation
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

RF power amplifier for W-CDMA base stations and multi carrier applications in the 920 MHz to 960 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain1		
2	drain2		1
3	gate1		<u> </u>
4	gate2		3 - 5
5	source [1]		4 7 4
		3 4	2 sym117

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage				
	Name	ame Description				
BLC9G10XS-120A	-	air cavity plastic earless flanged package; 4 leads	SOT1273-1			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+11	V
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature	<u>[1]</u>	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _{case} = 80 °C; I _{Dq} = 120 mA; V _{GS(am)peak} = 0.8 V		
		P _L = 18 W	0.349	k/W
		P _L = 28.2 W	0.301	k/W

Characteristics 6.

DC characteristics Table 6.

 $T_i = 25 \,^{\circ}$ C, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.4 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 40 mA	1.5	2.0	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 240 mA	1.5	2.17	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 28 V	-	-	1.4	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	8	-	А
I _{GSS}	gate leakage current	V _{GS} = 11 V	-	-	140	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 2 A	-	2.91	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.4 \text{ A}$	-	326	-	mΩ
Peak dev	rice					-
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.81 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 81mA	1.5	1.9	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 486 mA	1.5	2.0	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 28 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	15.7	-	А
I _{GSS}	gate leakage current	V _{GS} = 11 V	-	-	140	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 2 A	-	5.75	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.4 \text{ A}$	-	165	-	mΩ

Table 7. **RF** characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on CCDF; 3GPP test model 1; 64 DPCH; f_1 = 927.5 MHz; f_3 = 957.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak} = 0.8 \text{ V}$; $T_{case} = 25 \,^{\circ}\text{C}$; unless otherwise specified; in a Doherty production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G _p	power gain	P _{L(AV)} = 18 W	19.8	21	-	dB
η_{D}	drain efficiency	P _{L(AV)} = 18 W	44	49	-	%
RLin	input return loss	P _{L(AV)} = 18 W	-	-12	-8	dB
ACPR	adjacent channel power ratio	P _{L(AV)} = 18 W	-	-32	-27	dBc

RF characteristics Table 8.

Test signal: pulsed CW; t_p = 100 μ s; δ = 10 %; f = 960 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 120 mA (main); $V_{GS(amp)peak}$ = 0.8 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 925 MHz to 960 MHz

Symbo	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(3dB)}	output power at 3 dB gain compression		125	140	-	W

7. Test information

7.1 Ruggedness in Doherty operation

The BLC9G10XS-120A is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V; P_{L} = 100 W (CW); f = 925 MHz; tested on the Doherty development circuit.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 240 mA (main); V_{DS} = 28 V; typical values unless otherwise specified.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [3]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum pov	ver load				
920	1.15 – j5.18	4.33 + j1.33	66.0	67.8	22.7
940	1.59 – j5.92	4.33 + j1.33	65.0	67.6	23.0
960	2.56 – j6.94	3.93 + j1.22	63.0	64.8	22.8
Maximum dra	in efficiency load				
920	1.15 – j5.18	3.89 + j4.44	46.8	78.4	25.1
940	1.59 – j5.92	3.09 + j4.94	38.0	78.5	25.8
960	2.56 – j6.94	3.24 + j4.34	41.7	75.7	25.3

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 480 mA (peak); V_{DS} = 28 V; typical values unless otherwise specified.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G p [3]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum pov	ver load				
920	1.81 – j5.01	2.32 – j0.81	149.0	70.2	22.4
940	2.05 – j5.52	2.40 - j0.27	150.3	73.55	22.88
960	2.78 – j6.29	2.32 – j0.81	141.0	69.5	22.7
Maximum dra	in efficiency load				
920	1.81 – j5.01	2.30 + j1.69	79.4	84.3	26.2
940	2.05 – j5.52	2.32 + j1.69	97.7	84.5	25.8
960	2.78 – j6.29	2.16 + j1.33	91.2	84.0	25.8

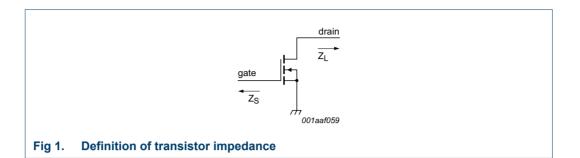
^[1] Z_S and Z_L defined in Figure 1.

^[2] At 3 dB gain compression.

^[3] At 6 dB OBO.

^[2] At 3 dB gain compression.

^[3] At 6 dB OBO.



7.3 Test circuit

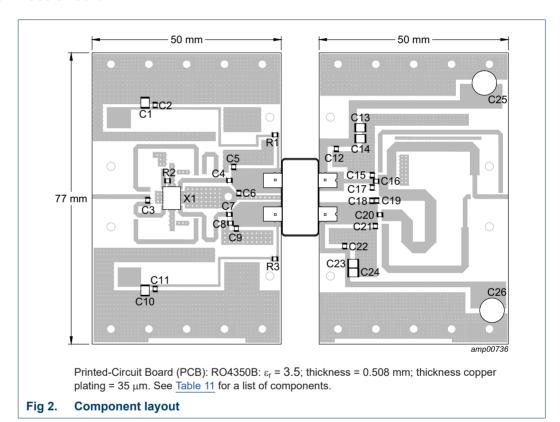


Table 11. List of components

See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C10, C13, C14, C23, C24	multilayer ceramic chip capacitor	4.7 μF, 100 V	Murata 1210
C2, C3, C4, C7, C11, C12, C22	multilayer ceramic chip capacitor	100 pF [1]	ATC600F
C5	multilayer ceramic chip capacitor	6.8 pF [1]	ATC600F
C6	multilayer ceramic chip capacitor	3.6 pF [1]	ATC600F
C8, C15	multilayer ceramic chip capacitor	3.0 pF [1]	ATC600F
C9, C19	multilayer ceramic chip capacitor	4.3 pF [1]	ATC600F
C16	multilayer ceramic chip capacitor	33 pF [1]	ATC600F

Table 11. List of components ...continued

See Figure 2 for component layout.

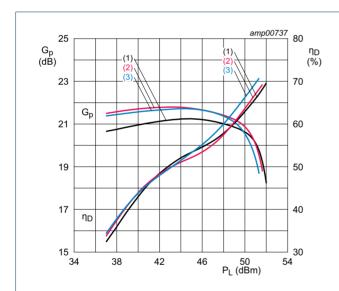
Component	Description	Value	Remarks
C17, C18	multilayer ceramic chip capacitor	3.9 pF [1]	ATC600F
C20	multilayer ceramic chip capacitor	2.0 pF [1]	ATC600F
C21	multilayer ceramic chip capacitor	6.2 pF [1]	ATC600F
C25, C26	electrolytic capacitor	1000 μF, 100 V	
R1, R3	chip resistor	5.1 Ω	SMD 0805
R2	chip resistor	50 Ω	SMD 0805
X1	asymmetric coupler	2 dB	RN2 CMX09Q02

^[1] Murata or capacitor of same quality

7.4 Graphical data

All data measured on the Doherty development circuit.

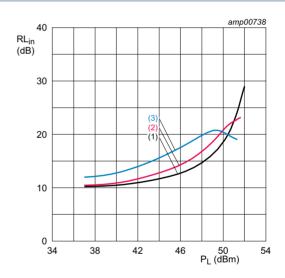
7.4.1 CW



 V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V.

- (1) f = 925 MHz
- (2) f = 943MHz
- (3) f = 960 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

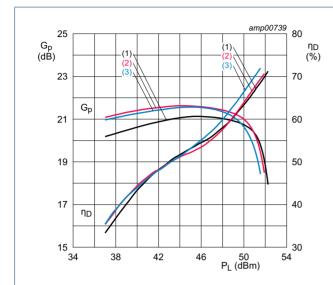


 V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V; t_p = 100 μ s; δ = 10 %.

- (1) f = 925 MHz
- (2) f = 943 MHz
- (3) f = 960 MHz

Fig 4. Input return loss as a function of output power; typical values

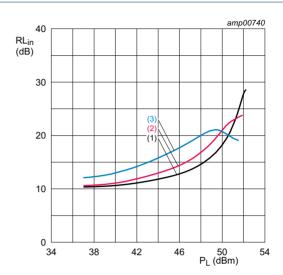
7.4.2 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V; t_p = 100 $\mu s;$ δ = 10 %.

- (1) f = 925 MHz
- (2) f = 943MHz
- (3) f = 960 MHz

Fig 5. Power gain and drain efficiency as function of output power; typical values

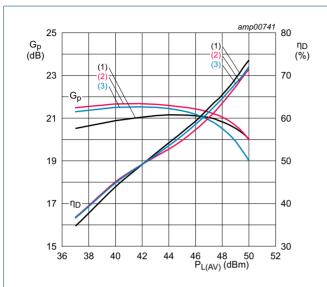


 V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V; t_p = 100 $\mu s;$ δ = 10 %.

- (1) f = 925 MHz
- (2) f = 943 MHz
- (3) f = 960 MHz

Fig 6. Input return loss as a function of output power; typical values

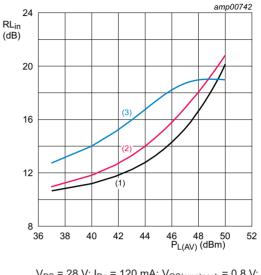
7.4.3 1-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V; 46 % clipping.

- (1) f = 925 MHz
- (2) f = 943 MHz
- (3) f = 960 MHz

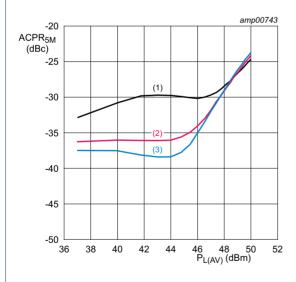
Fig 7. Power gain and drain efficiency as function of average output power; typical values



 V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V; 46 % clipping.

- (1) f = 925 MHz
- (2) f = 943MHz
- (3) f = 960 MHz

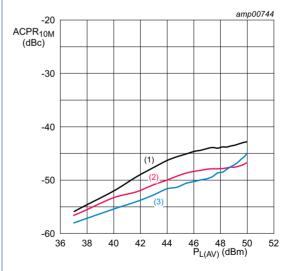
Fig 8. Input return loss as a function of average output power; typical values



 V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V; 46 % clipping.

- (1) f = 925 MHz
- (2) f = 943 MHz
- (3) f = 960 MHz

Fig 9. Adjacent channel power ratio (5 MHz) as a function of average output power; typical values

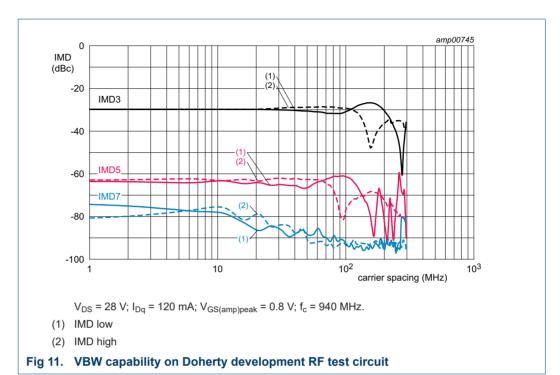


 V_{DS} = 28 V; I_{Dq} = 120 mA; $V_{GS(amp)peak}$ = 0.8 V; 46 % clipping.

- (1) f = 925 MHz
- (2) f = 943 MHz
- (3) f = 960 MHz

Fig 10. Adjacent channel power ratio (10 MHz) as a function of average output power; typical values

7.4.4 2-Tone VBW



8. Package outline

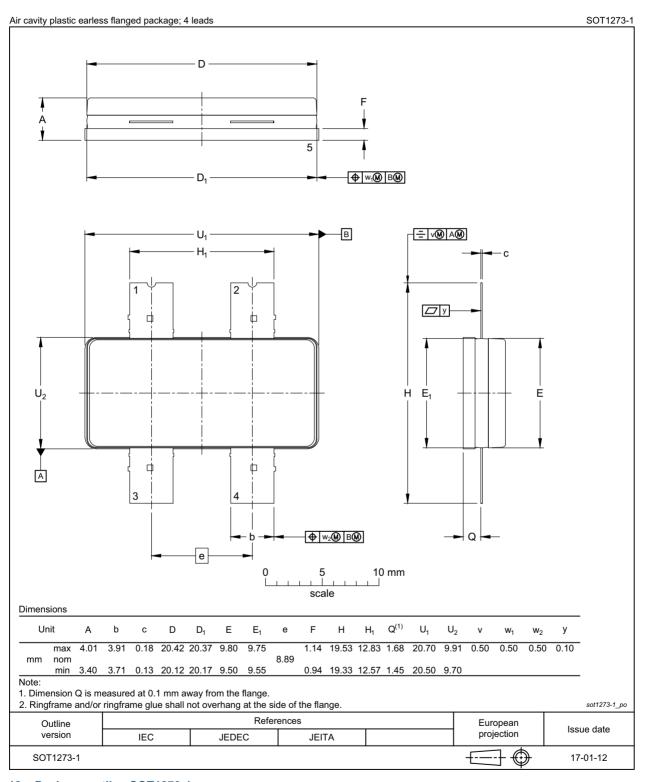


Fig 12. Package outline SOT1273-1

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

10. Abbreviations

Table 13. Abbreviations

Acronym	Description		
3GPP	3rd Generation Partnership Project		
CCDF	Complementary Cumulative Distribution Function		
CW	Continuous Wave		
DPCH	Dedicated Physical CHannel		
ESD	ElectroStatic Discharge		
LDMOS	Laterally Diffused Metal Oxide Semiconductor		
MTF	Median Time to Failure		
ОВО	Output Back Off		
PAR	Peak-to-Average Ratio		
RoHS	Restriction of Hazardous Substances		
SMD	Surface Mounted Device		
VBW	Video BandWidth		
VSWR	Voltage Standing Wave Ratio		
W-CDMA	Wideband Code Division Multiple Access		

11. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G10XS-120A v.1	20181129	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Power LDMOS transistor

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13. Contact information

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BLC9G10XS-120A

Power LDMOS transistor

14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
2	Pinning information 2
3	Ordering information
4	Limiting values
5	Thermal characteristics
6	Characteristics
7	Test information 4
7.1	Ruggedness in Doherty operation 4
7.2	Impedance information 4
7.3	Test circuit5
7.4	Graphical data 6
7.4.1	CW 6
7.4.2	Pulsed CW
7.4.3	1-Carrier W-CDMA 8
7.4.4	2-Tone VBW
8	Package outline
9	Handling information 11
10	Abbreviations
11	Revision history 11
12	Legal information
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Trademarks13
13	Contact information
14	Contents

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